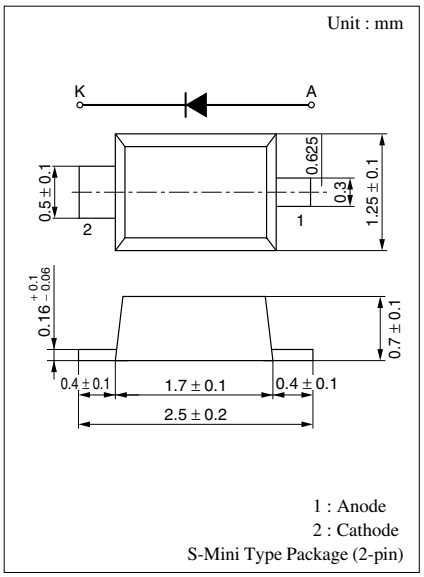
MA2J112

Silicon epitaxial planar type

For switching circuits



Marking Symbol: 1C

■ Features

- Small S-mini type package, allowing high-density mounting
- Ensuring the average forward current capacity $I_{F(AV)}$ = 200 mA

■ Absolute Maximum Ratings T_a = 25°C

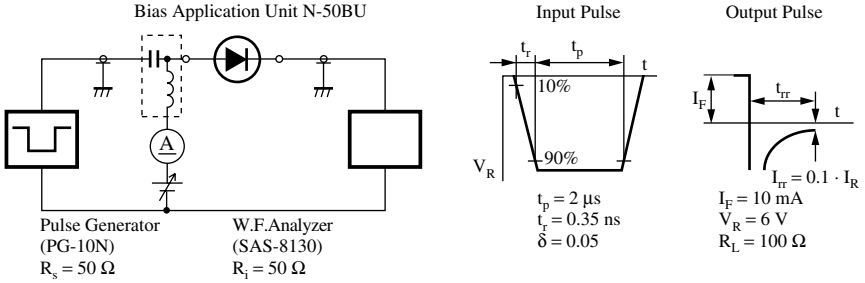
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Peak reverse voltage	V_{RM}	40	V
Average forward current*1	$I_{F(AV)}$	200	mA
Peak forward current	I_{FM}	600	mA
Non-repetitive peak forward surge current*2	I_{FSM}	1	A
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Note) *1 : With a printed-circuit board
*2 : t = 1 s

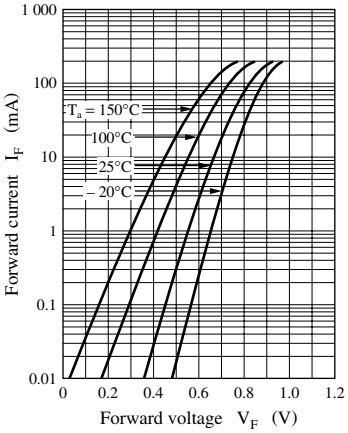
■ Electrical Characteristics T_a = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_{R1}	V_R = 15 V			50	nA
	I_{R2}	V_R = 35 V			500	nA
	I_{R3}	V_R = 35 V, T_a = 100°C			100	μA
Forward voltage (DC)	V_F	I_F = 200 mA			1.1	V
Terminal capacitance	C_t	V_R = 0 V, f = 1 MHz			4	pF
Reverse recovery time*	t_{rr}	I_F = 10 mA, V_R = 6 V I_{rr} = 0.1 · I_R, R_L = 100 Ω			10	ns

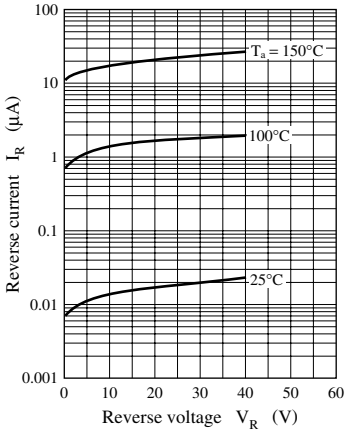
Note) 1. Rated input/output frequency: 100 MHz
2. * : t_{rr} measuring circuit



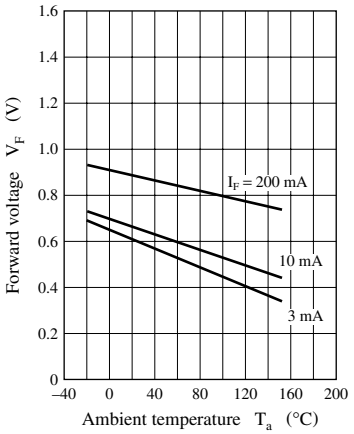
I_F — V_F



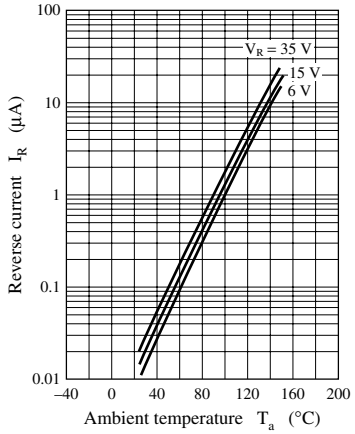
I_R — V_R



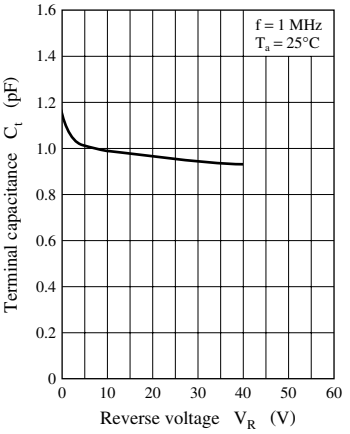
V_F — T_a



I_R — T_a



C_t — V_R



$I_{F(surge)}$ — t_W